

SCT2750NY

N-channel SiC power MOSFET

V _{DSS}	1700V
R _{DS(on)} (Typ.)	$750 m\Omega$
Ι _D	6A
P _D	57W

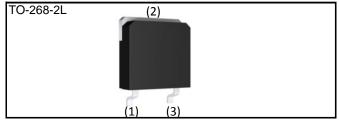
Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Long creepage distance with no center lead
- 4) Simple to drive
- 5) Pb-free lead plating ; RoHS compliant

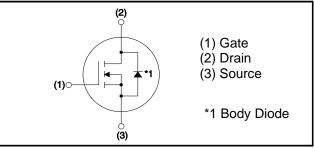
Application

- Auxilialy power supplies
- •Switch mode power supplies

Outline



Inner circuit



Packaging specifications

Туре	Packing	Embossed tape
	Reel size (mm)	330
	Tape width (mm)	24
	Basic ordering unit (pcs)	400
	Taping code	ТВ
	Marking	SCT2750NY

●Absolute maximum ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit	
Drain - Source voltage		V _{DSS}	1700	V
Continuous drain current	$T_c = 25^{\circ}C$	۱ _D *1	5.9	A
Continuous drain current	$T_c = 100^{\circ}C$	ا _D *1	4	А
Pulsed drain current	I _{D,pulse} *2	14	А	
Gate - Source voltage (DC)	V _{GSS}	-6 to 22	V	
Gate - Source surge voltage (t _{surge}	V_{GSS_surge} *3	-10 to 26	V	
Power dissipation $(T_c = 25^{\circ}C)$	P _D	57	W	
Junction temperature	Tj	175	°C	
Range of storage temperature	T _{stg}	-55 to +175	°C	

•Thermal resistance

Parameter	Symbol -		Unit		
	Symbol	Min.	Тур.	Max.	Onic
Thermal resistance, junction - case	R _{thJC}	-	2.04	2.65	°C/W

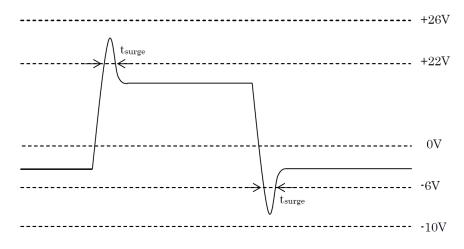
•Electrical characteristics ($T_a = 25^{\circ}C$)

Parameter	Symbol	Conditions		Unit		
Faranieter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_D = 1mA$	1700	-	-	V
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 1700V, V_{GS} = 0V$ $T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$	-	0.1 0.2	10 -	μΑ
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current I _{GSS-}		$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	$V_{GS (th)}$	$V_{DS} = V_{GS}, I_{D} = 0.63 mA$	1.6	2.8	4.0	V

*1 Limited only by maximum temperature allowed.

*2 PW \leq 10 μ s, Duty cycle \leq 1%

*3 Example of acceptable Vgs waveform



*4 Pulsed

•Electrical characteristics ($T_a = 25^{\circ}C$)

Deremeter	Currente al	Conditions		Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
		$V_{GS} = 18V, I_{D} = 1.7A$				
Static drain - source on - state resistance	R _{DS(on)} *4	$T_j = 25^{\circ}C$	-	750	975	mΩ
		T _j = 125°C	-	1088	-	
Gate input resistance	R _G	f = 1MHz, open drain	-	49	-	Ω
Transconductance	g _{fs} *4	$V_{DS} = 10V, I_{D} = 1.7A$	-	0.6	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	275	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	19	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	7	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 800V	-	21	-	pF
Turn - on delay time	t _{d(on)} *4	$V_{DD} = 500V, I_{D} = 1.7A$	-	19	-	
Rise time	t _r *4	V _{GS} = 18V/0V	-	24	-	
Turn - off delay time	t _{d(off)} *4	$R_L = 294\Omega$	-	41	-	ns
Fall time	t _f *4	$R_{G} = 0\Omega$	-	63	-	
Turn - on switching loss	E _{on} *4	$V_{DD} = 800V, I_{D} = 1.7A$ $V_{GS} = 18V/0V$	-	76	-	1
Turn - off switching loss	E _{off} *4	R _G = 0Ω, L=2mH *E _{on} includes diode reverse recovery	-	33	-	μJ

•Gate Charge characteristics ($T_a = 25^{\circ}C$)

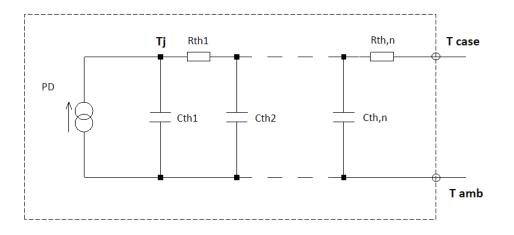
Deremeter	Sumbol	Conditions		Unit		
Parameter Symbo		Conditions	Min.	Тур.	Max.	Unit
Total gate charge	Q_g^{*4}	V _{DD} = 500V	-	17	-	
Gate - Source charge	Q_{gs}^{*4}	I _D = 1.5A	-	5	-	nC
Gate - Drain charge	Q_{gd}^{*4}	V _{GS} = 18V	-	6.5	-	
Gate plateau voltage	V _(plateau)	$V_{DD} = 500V, I_D = 1.5A$	-	11.0	-	V

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions		Unit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Inverse diode continuous, forward current	ا _S *1	T _c = 25°C	-	-	5.9	А
Inverse diode direct current, pulsed	I _{SM} *2	T _c = 25 C	-	-	14	A
Forward voltage	V_{SD} *4	$V_{GS} = 0V, I_{S} = 1.7A$	-	4.3	-	V
Reverse recovery time	t _{rr} *4		-	26	-	ns
Reverse recovery charge	Q _{rr} ^{*4}	I _F = 1.7A, V _R = 800V di/dt = 290A/μs	-	18	-	nC
Peak reverse recovery current	^{*4}		-	1.3	-	А

•Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
R _{th1}	243m		C_{th1}	352µ	
R _{th2}	1529m	K/W	C_{th2}	1.57m	Ws/K
R _{th3}	268m		C _{th3}	68.7m	



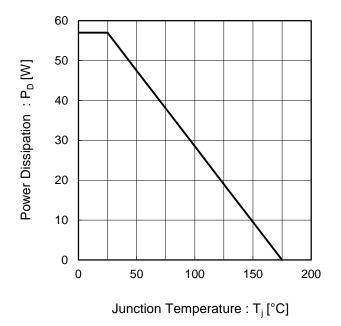


Fig.1 Power Dissipation Derating Curve

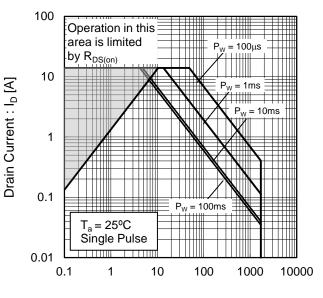
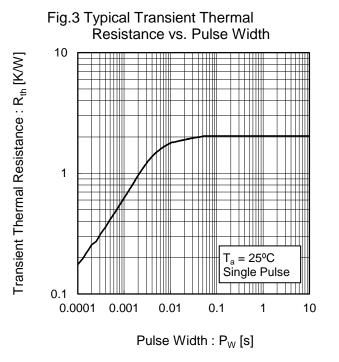


Fig.2 Maximum Safe Operating Area

Drain - Source Voltage : V_{DS} [V]



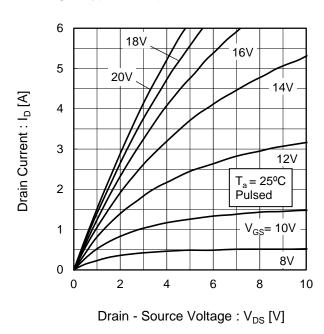
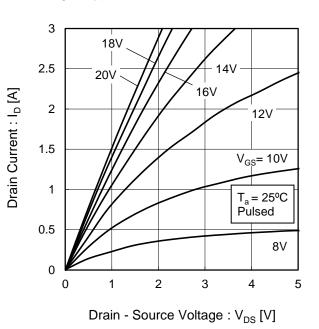
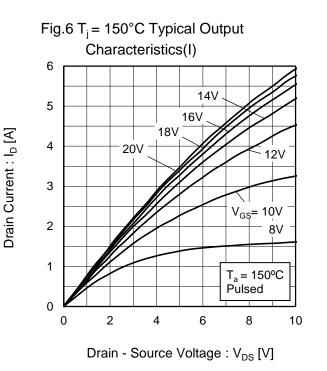
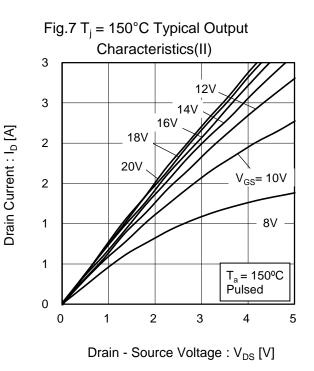


Fig.4 Typical Output Characteristics(I)

Fig.5 Typical Output Characteristics(II)







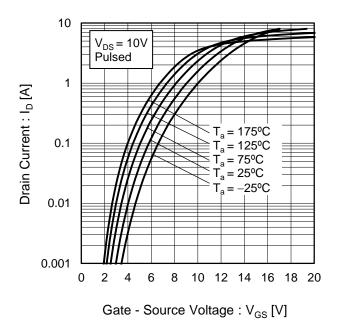
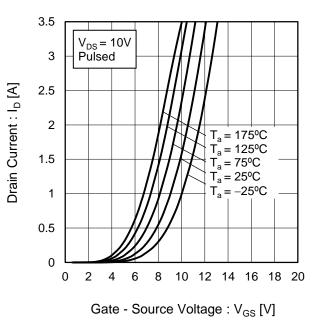


Fig.8 Typical Transfer Characteristics (I)

Fig.9 Typical Transfer Characteristics (II)



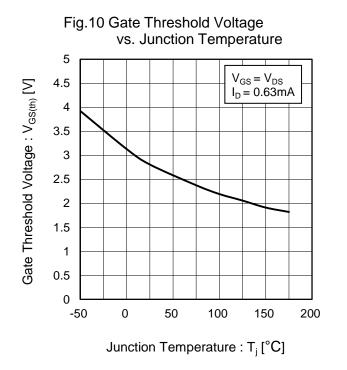
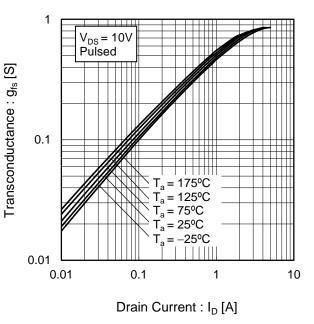


Fig.11 Transconductance vs. Drain Current



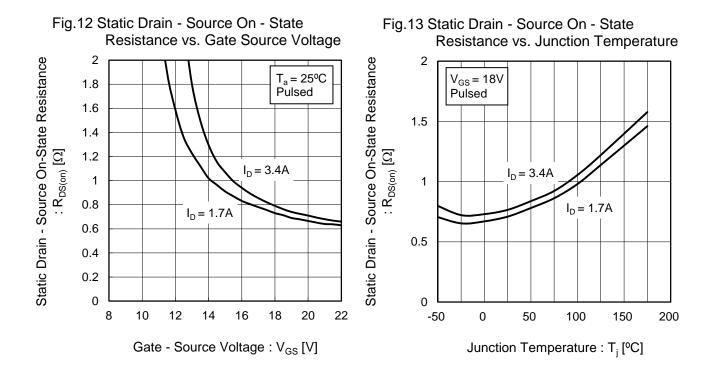


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current Static Drain - Source On-State Resistance 10 : R_{DS(on)} [Ω] 1 T_a = 175°C T_a = 125°C $T_{a}^{"} = 75^{\circ}C$ $V_{GS} = 18V$ T_a = 25⁰C Pulsed $T_a = -25^{\circ}C$ 0.1 0.1 1 10

Drain Current : I_D [A]

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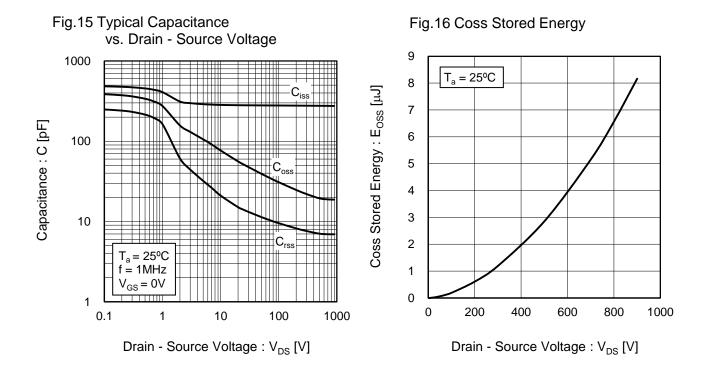
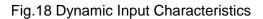
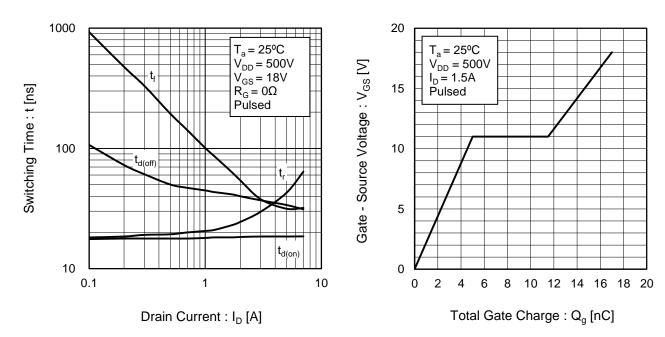
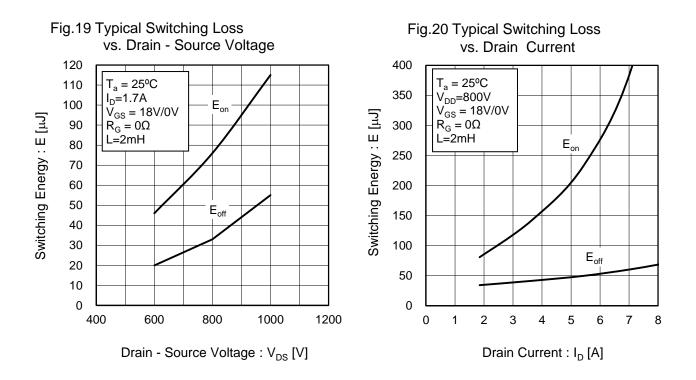


Fig.17 Switching Characteristics







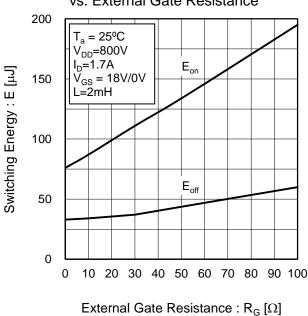
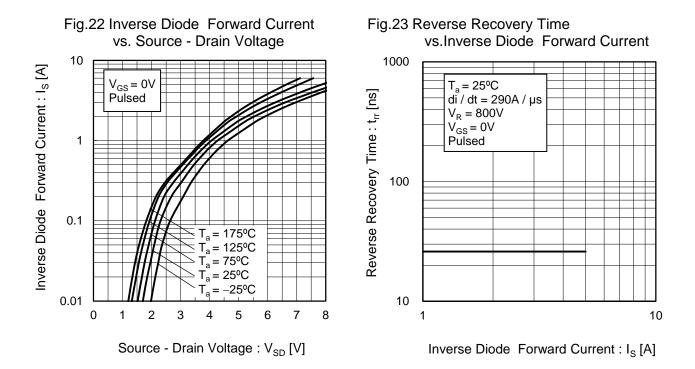


Fig.21 Typical Switching Loss vs. External Gate Resistance



Measurement circuits

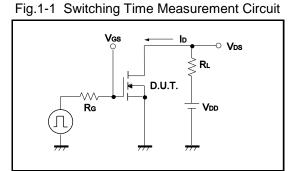


Fig.2-1 Gate Charge Measurement Circuit

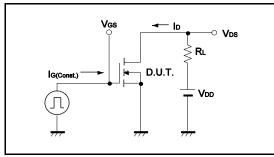


Fig.3-1 Switching Energy Measurement Circuit

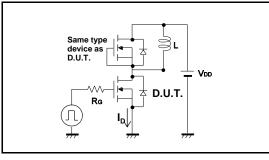
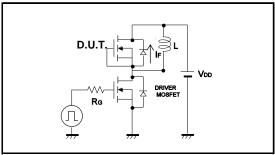


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform





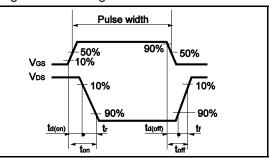


Fig.2-2 Gate Charge Waveform

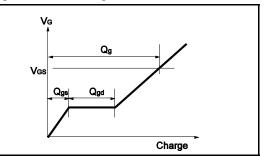
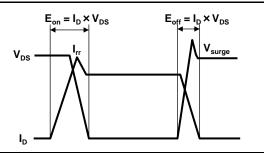
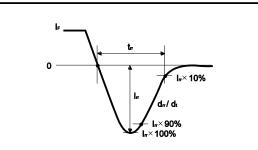


Fig.3-2 Switching Waveforms

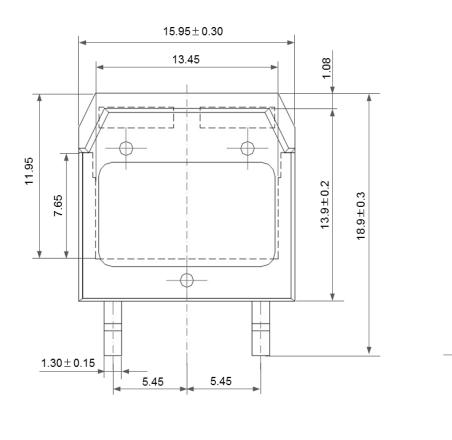




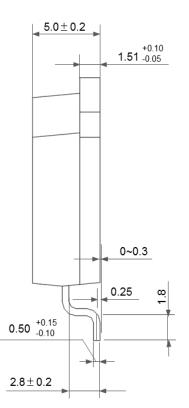


•Dimensions (Unit : mm)

TO-268-2L







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SCT2750NY - Web Page

Distribution Inventory

Part Number	SCT2750NY
Package	TO-268-2L
Unit Quantity	800
Minimum Package Quantity	800
Packing Type	Taping
Constitution Materials List	inquiry
RoHS	Yes